V_{RSM}	=	5500	V
$I_{F(AV)M}$	=	3480	A
$I_{F(RMS)}$	=	5470	A
I_{FSM}	=	46×10^3	A
V_{F0}	=	0.94	V
r_F	=	0.147	mΩ

Rectifier Diode
5SDD 33L5500

Doc. No. 5SYA1168-00 March 05

- **Patented free-floating silicon technology**
- **Very low on-state losses**
- **Optimum power handling capability**

Blocking

Maximum rated values [1)]

Parameter	Symbol	Conditions	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	f = 50 Hz, t_p = 10ms, T_j = 0...150°C	5000	V
Non-repetitive peak reverse voltage	V_{RSM}	f = 5 Hz, t_p = 10ms, T_j = 0...150°C	5500	V

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Max. (reverse) leakage current	I_{RRM}	V_{RRM}, Tj = 150°C			400	mA

Mechanical data

Maximum rated values [1)]

Parameter	Symbol	Conditions	min	typ	max	Unit
Mounting force	F_M		63	70	77	kN
Acceleration	a	Device unclamped			50	m/s^2
Acceleration	a	Device clamped			100	m/s^2

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Weight	m				1.45	kg
Housing thickness	H	F_M = 70 kN, T_a = 25 °C	26.0		26.6	mm
Surface creepage distance	D_S		35			mm
Air strike distance	D_a		14			mm

1) Maximum rated values indicate limits beyond which damage to the device may occur

On-state

Maximum rated values [1)]

Parameter	Symbol	Conditions	min	typ	max	Unit
Max. average on-state current	$I_{F(AV)M}$	50 Hz, Half sine wave, T_C = 90 °C			3480	A
Max. RMS on-state current	$I_{F(RMS)}$				5470	A
Max. peak non-repetitive surge current	I_{FSM}	t_p = 10 ms, T_j = 150°C, V_R = 0 V			46×10^3	A
Limiting load integral	I^2t				10.6×10^6	A^2s
Max. peak non-repetitive surge current	I_{FSM}	t_p = 8.3 ms, T_j = 150°C, V_R = 0 V			49.2×10^3	A
Limiting load integral	I^2t				10.06×10^6	A^2s

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
On-state voltage	V_F	I_F = 5000 A, T_j = 150°C			1.68	V
Threshold voltage	$V_{(T0)}$	T_j = 150°C I_T = 3000...8000 A			0.94	V
Slope resistance	r_T				0.147	mΩ

Switching

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Recovery charge	Q_{rr}	di_F/dt = -10 A/µs, V_R = 200 V I_{FRM} = 4000 A, T_j = 150°C			10000	µAs

Thermal

Maximum rated values [1)]

Parameter	Symbol	Conditions	min	typ	max	Unit
Operating junction temperature range	T_{vj}		0		150	°C
Storage temperature range	T_{stg}		-40		150	°C

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Thermal resistance junction to case	$R_{th(j-c)}$	Double-side cooled F_m = 63...77 kN			7	K/kW
	$R_{th(j-c)A}$	Anode-side cooled F_m = 63...77 kN			14	K/kW
	$R_{th(j-c)C}$	Cathode-side cooled F_m = 63...77 kN			14	K/kW
Thermal resistance case to heatsink	$R_{th(c-h)}$	Double-side cooled F_m = 63...77 kN			1.5	K/kW
	$R_{th(c-h)}$	Single-side cooled F_m = 63...77 kN			3	K/kW

Analytical function for transient thermal impedance:

$$Z_{th(j-c)}(t) = \sum_{i=1}^{n} R_{th\,i}(1 - e^{-t/t_i})$$

i	1	2	3	4
$R_{th\,i}$(K/kW)	4.701	1.401	0.611	0.298
τ_i(s)	0.5463	0.0746	0.0087	0.0021

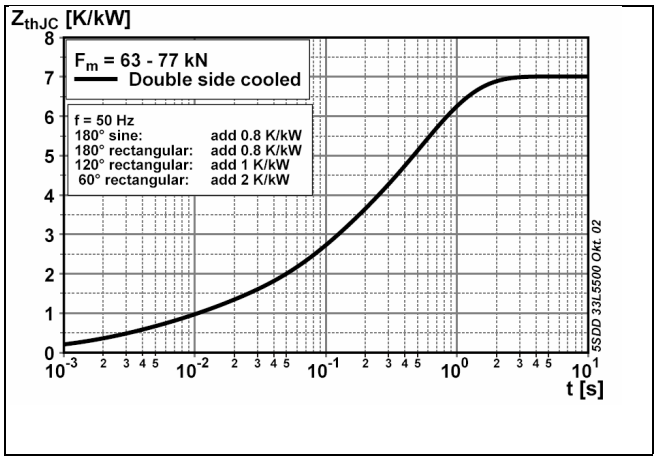

Fig. 1 Transient thermal impedance junction-to-case.

Max. on-state characteristic model:

$$V_{F25} = A_{Tvj} + B_{Tvj} \cdot I_F + C_{Tvj} \cdot \ln(I_F + 1) + D_{Tvj} \cdot \sqrt{I_F}$$

Valid for I_F = 300 – 70000 A

A_{25}	B_{25}	C_{25}	D_{25}
-352.00×10^{-6}	38.50×10^{-6}	127×10^{-3}	4.47×10^{-3}

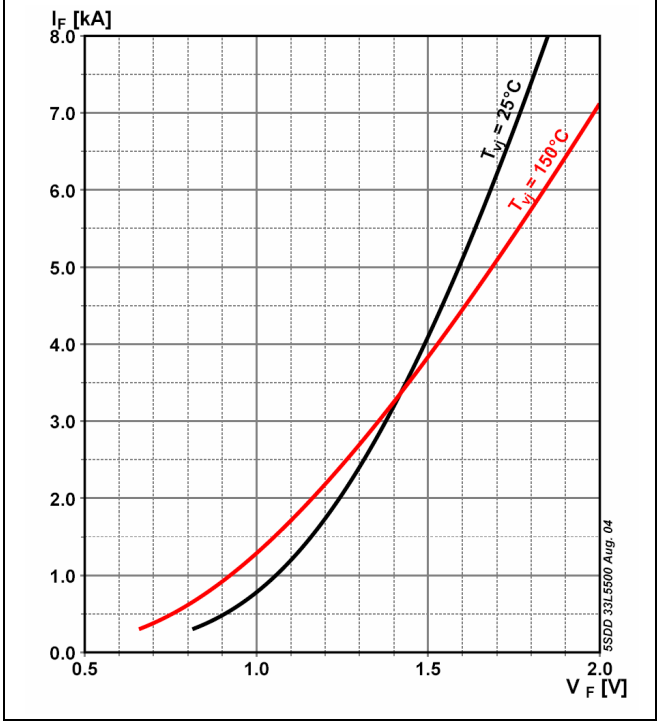

Fig. 2 Isothermal on-state characteristics

Max. on-state characteristic model:

$$V_{F150} = A_{Tvj} + B_{Tvj} \cdot I_F + C_{Tvj} \cdot \ln(I_F + 1) + D_{Tvj} \cdot \sqrt{I_F}$$

Valid for I_F = 300 – 70000 A

A_{150}	B_{150}	C_{150}	D_{150}
95.90×10^{-6}	89.80×10^{-6}	90.50×10^{-3}	6.60×10^{-3}

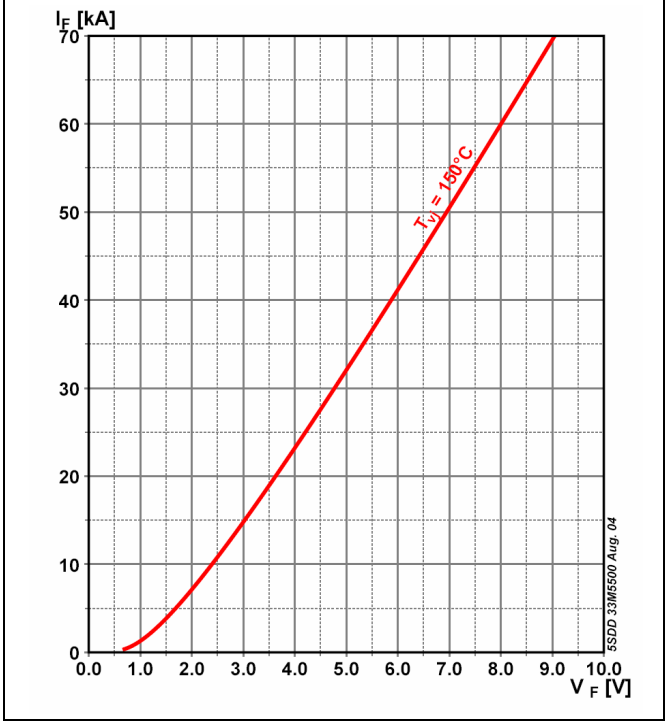

Fig. 3 Isothermal on-state characteristics

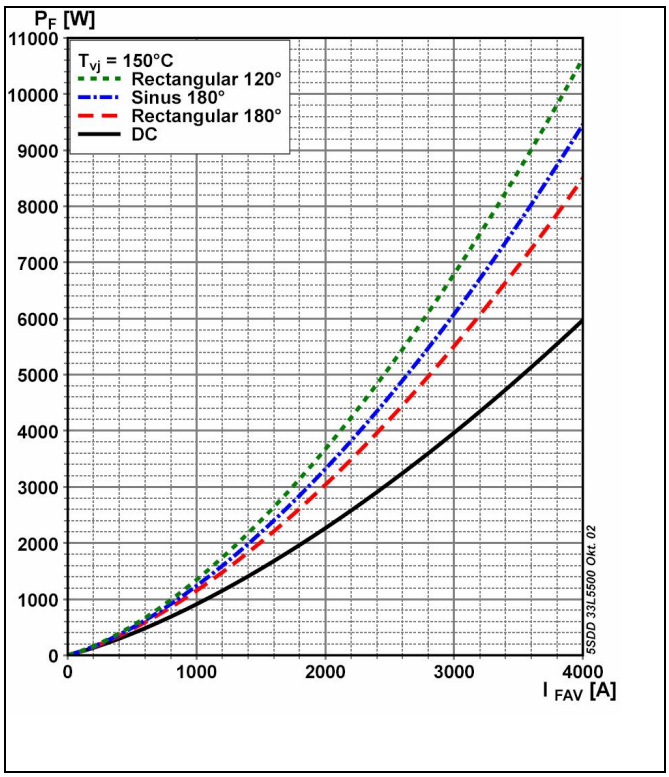

Fig. 4 On-state power losses vs average on-state current.

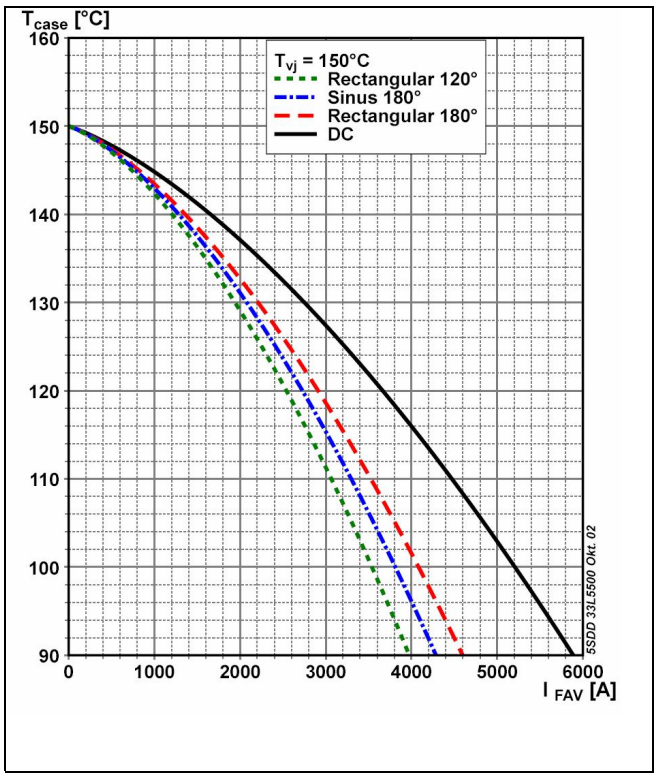

Fig. 5 Max. permissible case temperature vs average on-state current.

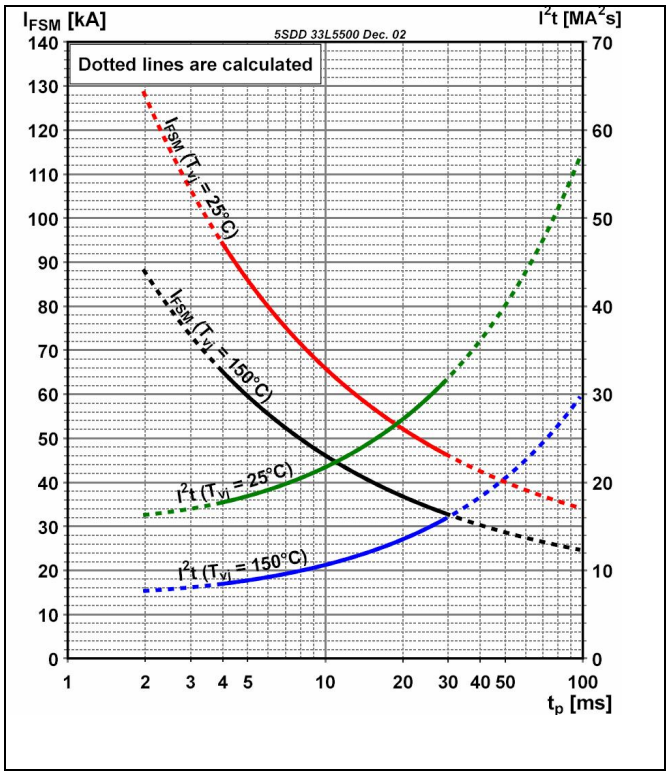

Fig. 6 Surge on-state current vs. number of pulses. Half-sine wave, 10 ms, 50Hz.

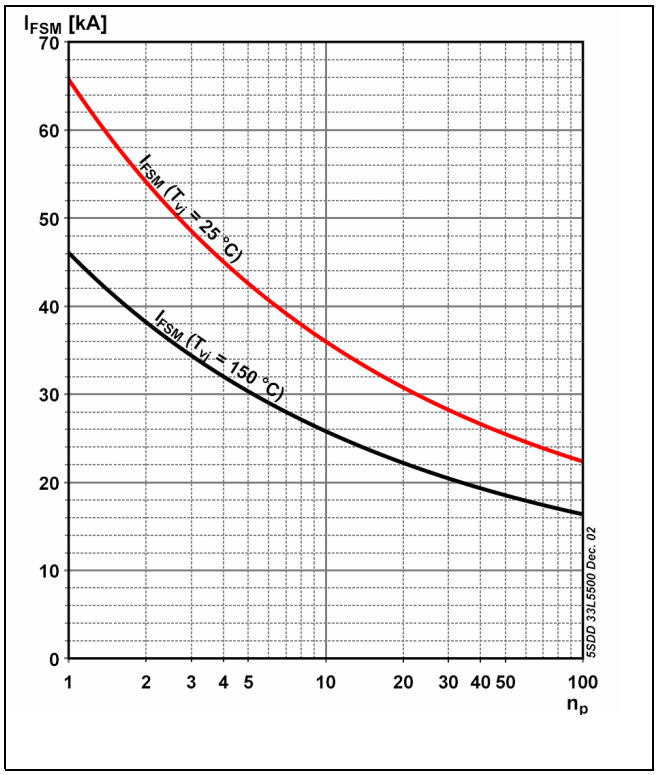

Fig. 7 Surge on-state current vs. number of pulses. Half-sine wave, 10 ms, 50Hz.

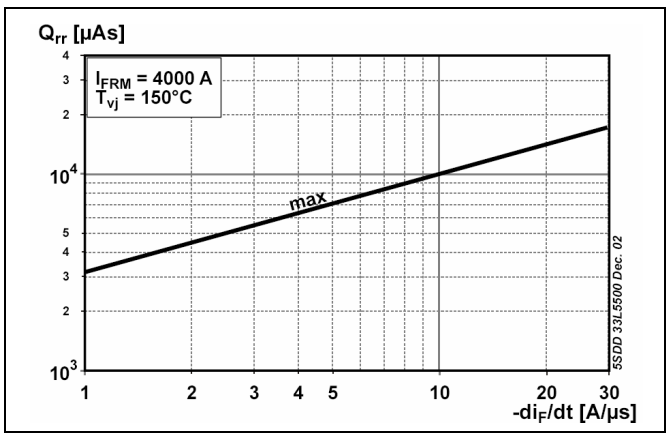

Fig. 8 Recovery charge vs. decay rate of on-state current.

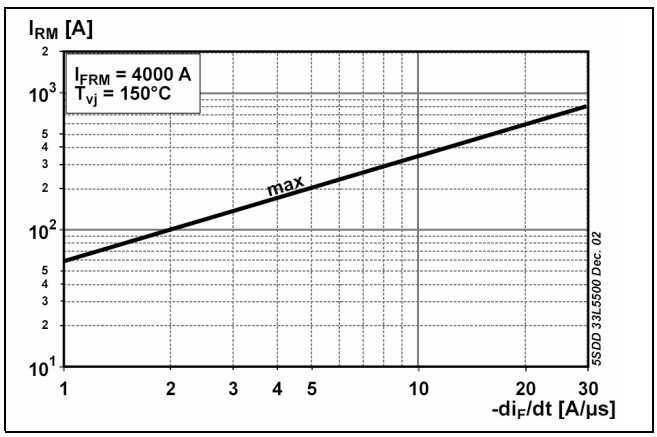

Fig. 9 Peak reverse recovery current vs. decay rate of on-state current.

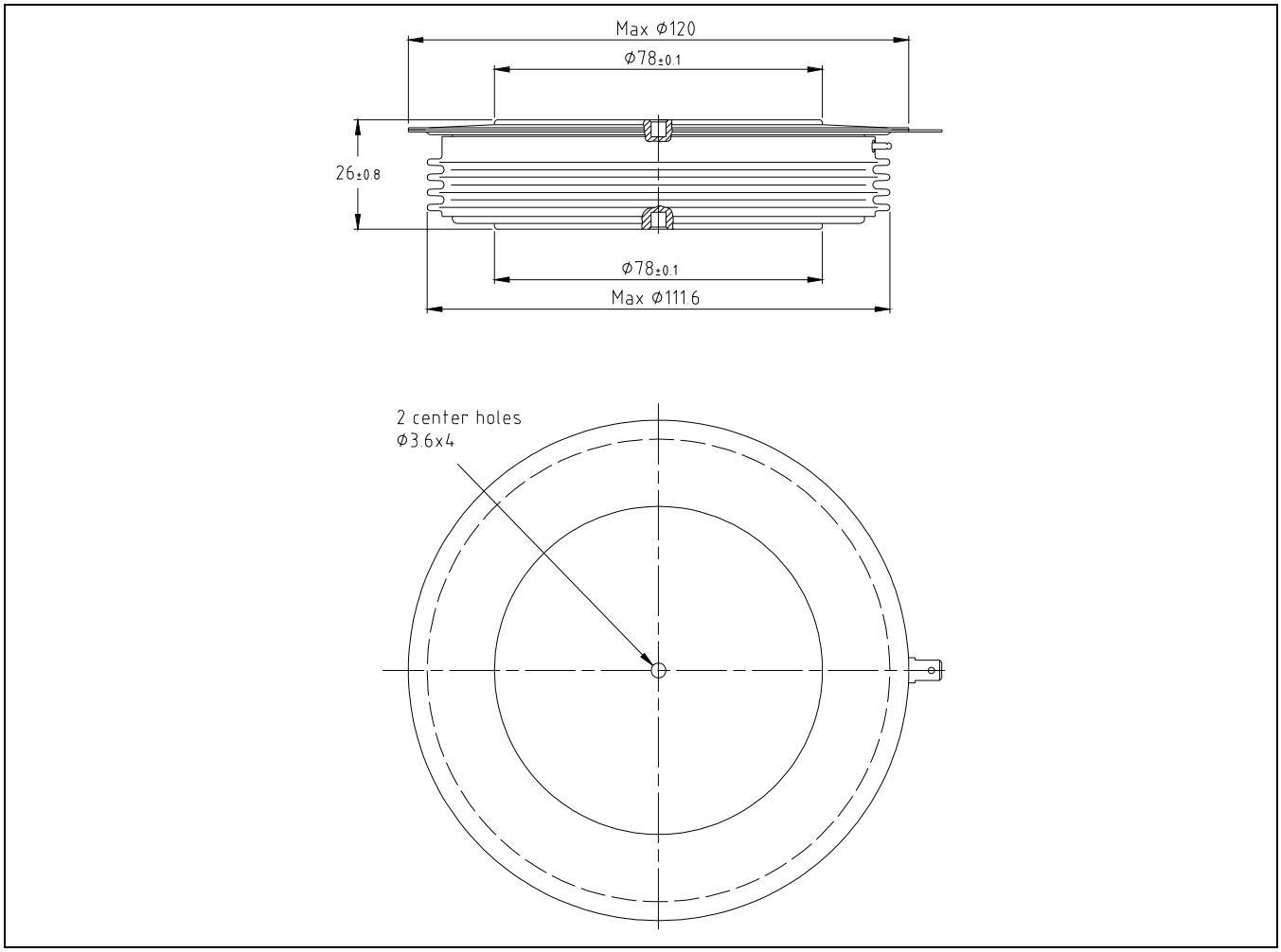

Fig. 10 Outline drawing. All dimensions are in millimeters and represent nominal values unless stated otherwise.

Related application notes:

Doc. Nr	Titel
5SYA 2020	Design of RC-Snubbers for Phase Control Applications
5SYA 2029	Designing Large Rectifiers with High Power Diodes
5SYA 2036	Recommendations regarding mechanical clamping of Press Pack High Power Semiconductors

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ABB Switzerland Ltd
Semiconductors
Fabrikstrasse 3
CH-5600 Lenzburg, Switzerland

Telephone +41 (0)58 586 1419
Fax +41 (0)58 586 1306
Email abbsem@ch.abb.com
Internet www.abb.com/semiconductors

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